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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/618,280	07/11/2003	Irfan Rahim	9818-075-999	4813
48591	7590	12/29/2004	EXAMINER	
MORGAN, LEWIS & BOCKIUS LLP 1111 PENNSYLVANIA AVENUE WASHINGTON, DC 20004			LAM, DAVID	
			ART UNIT	PAPER NUMBER
			2818	

DATE MAILED: 12/29/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

10/618,280

Applicant(s)

RAHIM ET AL.

Examiner

David Lam

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on ____.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-20 is/are pending in the application.
- 4a) Of the above claim(s) ____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) ____ is/are allowed.
- 6) ☒ Claim(s) 1,2,5-7,10-12,15,16,19 and 20 is/are rejected.
- 7) ☒ Claim(s) 3,4,8,9,13,14,17 and 18 is/are objected to.
- 8) ☐ Claim(s) ____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 11 July 2003 is/are: a) ☐ accepted or b) ☒ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. ____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date ____.
- 4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date. ____.
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: ____.

DETAILED ACTION

Drawings

1. Figure 5 should be designated by a legend such as --Prior Art-- because only that which is old is illustrated. See MPEP § 608.02(g). A proposed drawing correction or corrected drawings are required in reply to the Office action to avoid abandonment of the application. The objection to the drawings will not be held in abeyance.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

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2. Claims 1-2, 5-7, 10-12, 15-16 are rejected under 35 U.S.C. 102(e) as being anticipated by Tu et al. (6,515,899).

Regarding to claims 1-2, 5-7, 15-16, Tu et al. disclose a nonvolatile memory cell comprising: a high-voltage write path (62, Cr) coupled to high-voltage capacitor (C_G); a low-voltage read path (64, 74, 66) coupled to both the high-voltage capacitor and the high-voltage write path; wherein either the high-voltage write path is situated between the low-voltage read path and the high-voltage capacitor or the high-voltage capacitor is situated between the low-voltage read path and the high-voltage write path; wherein the low-voltage read path comprises a negative floating gate transistor (66) and a read transistor (64) are serially connected. *See Figs. 1-4; Cols. 1-4.*

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 19-20 rejected under 35 U.S.C. 103(a) as being unpatentable over Tu et al. (6,515,899).

Regarding to claims 19-20, Tu et al. disclose a nonvolatile memory device comprising: a high-voltage capacitor (C_G); a high-voltage writ path (62, Cr); a low-voltage read path (64, 74, 66); a floating gate (116) in a substrate (92).

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Tu et al. disclose the claimed invention as noted above but not explicitly disclose the high-voltage capacitor; the high-voltage write path and low-voltage read path comprising first, second and third diffusion, wherein the second region is situated between the first diffusion region and the third diffusion, or the first diffusion region is situated between the second diffusion region and the third region and a floating gate over the first, second and third diffusion regions.

However, Tu et al. disclose nonvolatile has N+ type region form with standard diffusion techniques that associated with the high-voltage capacitor, write path, low-voltage read path in the substrate (92). *See Figs. 1-4; Cols. 1-4.*

It would have been obvious to form first, second and third diffusion regions of the high-voltage capacitor, write path, low-voltage read path in the substrate and a floating gate over the first, second and third diffusion regions to increased drive current and extra protection to ensure read transistor is not damaged by high voltage.

Allowable Subject Matter

4. Claims 3-4, 8-9, 13-14, 17-18 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter: The prior art of record fails to teach wherein the high-voltage capacitor comprises a conductive plate that is separated from a first diffusion region by an oxide layer and is electrically connected to a floating gate of the floating gate transistor.

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Conclusion

5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure.

- Mehta et al. (5,969,992) disclose an EEPROM cell using P-well for tunneling across a channel.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Lam whose telephone number is 571-272-1782. The examiner can normally be reached on 6:00 – 4:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Nelms can be reached on 571-272-1787. The fax phone numbers for the organization where this application or proceeding is assigned is (703) 872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-27-9197 (toll-free).

D. Lam

December 20, 2004



**DAVID LAM
PRIMARY EXAMINER**